



FGH80N60FD

600V, 80A Field Stop IGBT

Features

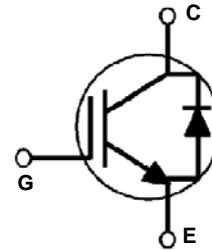
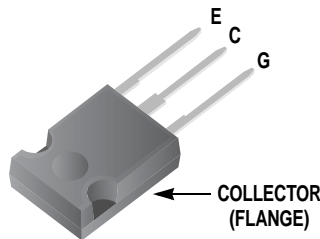
- High current capability
- Low saturation voltage: $V_{CE(sat)} = 1.8V @ I_C = 40A$
- High input impedance
- Fast switching
- RoHS compliant

General Description

Using Novel Field Stop IGBT Technology, Fairchild's new series of Field Stop IGBTs offer the optimum performance for Induction Heating applications where low conduction and switching losses are essential.

Applications

- Induction Heating Application



Absolute Maximum Ratings

Symbol	Description	Ratings	Units
V_{CES}	Collector-Emitter Voltage	600	V
V_{GES}	Gate-Emitter Voltage	± 20	V
I_C	Collector Current @ $T_C = 25^\circ C$	80	A
	Collector Current @ $T_C = 100^\circ C$	40	A
$I_{CM} (1)$	Pulsed Collector Current @ $T_C = 25^\circ C$	160	A
P_D	Maximum Power Dissipation @ $T_C = 25^\circ C$	290	W
	Maximum Power Dissipation @ $T_C = 100^\circ C$	116	W
T_J	Operating Junction Temperature	-55 to +150	$^\circ C$
T_{stg}	Storage Temperature Range	-55 to +150	$^\circ C$
T_L	Maximum Lead Temp. for soldering Purposes, 1/8" from case for 5 seconds	300	$^\circ C$

Notes :

(1) Repetitive rating : Pulse width limited by max. junction temperature

Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Units
$R_{\theta JC}(IGBT)$	Thermal Resistance, Junction-to-Case	--	0.43	$^\circ C/W$
$R_{\theta JC}(Diode)$	Thermal Resistance, Junction-to-Case	--	1.5	$^\circ C/W$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	--	40	$^\circ C/W$

Package Marking and Ordering Information

Device Marking	Device	Package	Packaging Type	Qty per Tube	Max Qty per Box
FGH80N60FD	FGH80N60FDTU	TO-247	Tube	30ea	-

Electrical Characteristics of the IGBT T_C = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
Off Characteristics						
V_{CES}	Collector-Emitter Breakdown Voltage	$V_{GE} = 0V, I_C = 250\mu A$	600	--	--	V
$\frac{\Delta BV_{CES}}{\Delta T_J}$	Temperature Coefficient of Breakdown Voltage	$V_{GE} = 0V, I_C = 250\mu A$	--	0.6	--	V/°C
I_{CES}	Collector Cut-Off Current	$V_{CE} = V_{CES}, V_{GE} = 0V$	--	--	250	μA
I_{GES}	G-E Leakage Current	$V_{GE} = V_{GES}, V_{CE} = 0V$	--	--	± 400	nA
On Characteristics						
$V_{GE(th)}$	G-E Threshold Voltage	$I_C = 250\mu A, V_{CE} = V_{GE}$	4.5	5.5	7.0	V
$V_{CE(sat)}$	Collector to Emitter Saturation Voltage	$I_C = 40A, V_{GE} = 15V$	--	1.8	2.4	V
		$I_C = 40A, V_{GE} = 15V, T_C = 125^\circ C$	--	2.05	--	V
Dynamic Characteristics						
C_{ies}	Input Capacitance	$V_{CE} = 30V, V_{GE} = 0V, f = 1MHz$	--	2110	--	pF
C_{oes}	Output Capacitance		--	200	--	pF
C_{res}	Reverse Transfer Capacitance		--	60	--	pF
Switching Characteristics						
$t_{d(on)}$	Turn-On Delay Time	$V_{CC} = 400V, I_C = 40A, R_G = 10\Omega, V_{GE} = 15V, \text{Inductive Load}, T_C = 25^\circ C$	--	21	--	ns
t_r	Rise Time		--	56	--	ns
$t_{d(off)}$	Turn-Off Delay Time		--	126	--	ns
t_f	Fall Time		--	50	100	ns
E_{on}	Turn-On Switching Loss		--	1	1.5	mJ
E_{off}	Turn-Off Switching Loss		--	0.52	0.78	mJ
E_{ts}	Total Switching Loss	--	1.52	2.28	mJ	
$t_{d(on)}$	Turn-On Delay Time	$V_{CC} = 400V, I_C = 40A, R_G = 10\Omega, V_{GE} = 15V, \text{Inductive Load}, T_C = 125^\circ C$	--	20	--	ns
t_r	Rise Time		--	54	--	ns
$t_{d(off)}$	Turn-Off Delay Time		--	131	--	ns
t_f	Fall Time		--	70	--	ns
E_{on}	Turn-On Switching Loss		--	1.1	--	mJ
E_{off}	Turn-Off Switching Loss		--	0.78	--	mJ
E_{ts}	Total Switching Loss	--	1.88	--	mJ	
Q_g	Total Gate Charge	$V_{CE} = 400V, I_C = 40A, V_{GE} = 15V$	--	120	--	nC
Q_{ge}	Gate-Emitter Charge		--	14	--	nC
Q_{gc}	Gate-Collector Charge		--	58	--	nC

Electrical Characteristics of the Diode $T_C = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max	Units	
V_{FM}	Diode Forward Voltage	$I_F = 20\text{A}$	$T_C = 25^\circ\text{C}$	-	2.3	2.8	V
			$T_C = 125^\circ\text{C}$	-	1.7	-	
t_{rr}	Diode Reverse Recovery Time	$I_{ES} = 20\text{A}, dI_{ES}/dt = 200\text{A}/\mu\text{s}$	$T_C = 25^\circ\text{C}$	-	36	-	ns
			$T_C = 125^\circ\text{C}$	-	105	-	
I_{rr}	Diode Reverse Recovery Current	$I_{ES} = 20\text{A}, dI_{ES}/dt = 200\text{A}/\mu\text{s}$	$T_C = 25^\circ\text{C}$	-	2.6	-	A
			$T_C = 125^\circ\text{C}$	-	7.8	-	
Q_{rr}	Diode Reverse Recovery Charge	$I_{ES} = 20\text{A}, dI_{ES}/dt = 200\text{A}/\mu\text{s}$	$T_C = 25^\circ\text{C}$	-	46.8	-	nC
			$T_C = 125^\circ\text{C}$	-	409	-	

Typical Performance Characteristics

Figure 1. Typical Output Characteristics

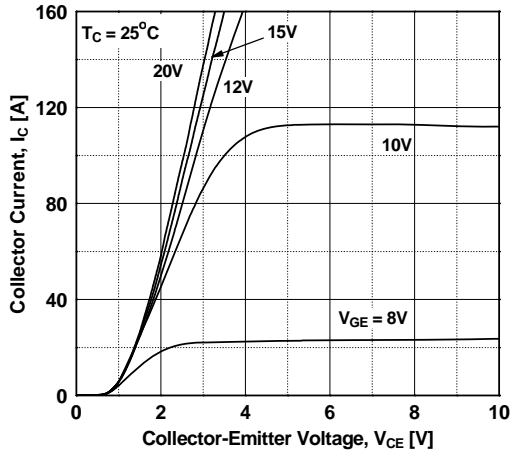


Figure 2. Typical Saturation Voltage Characteristics

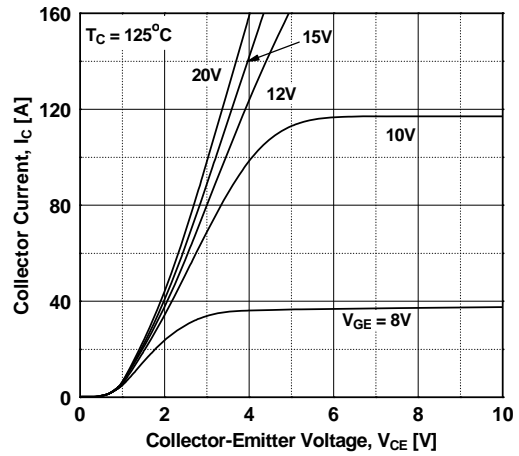


Figure 3. Typical Saturation Voltage Characteristics

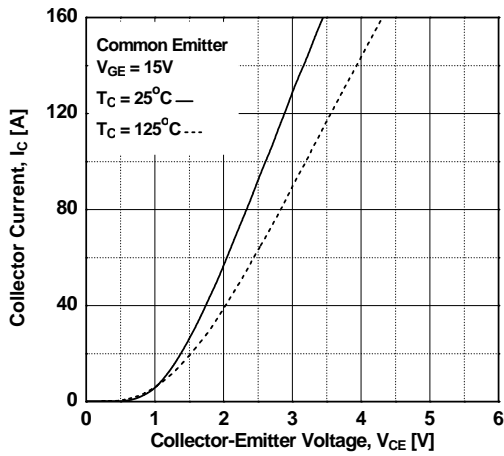


Figure 4. Transfer Characteristics

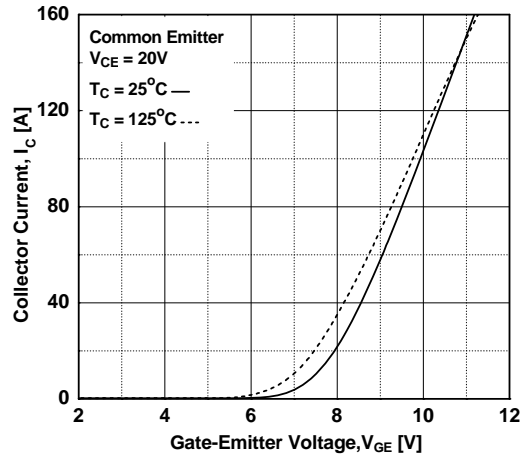


Figure 5. Saturation Voltage vs. Case

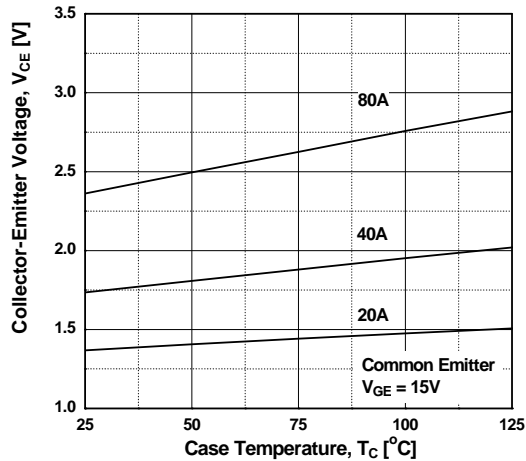
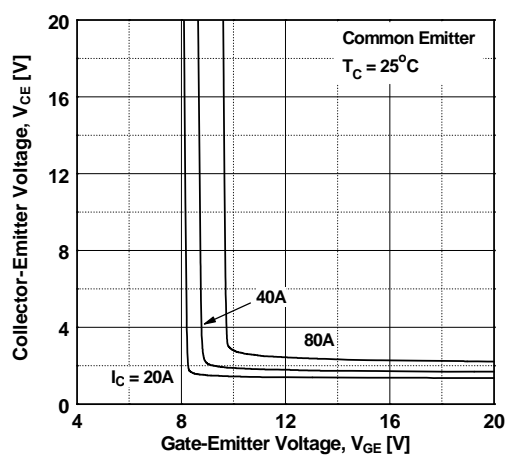


Figure 6. Saturation Voltage vs. Vge



Typical Performance Characteristics (Continued)

Figure 7. Saturation Voltage vs. V_{GE}

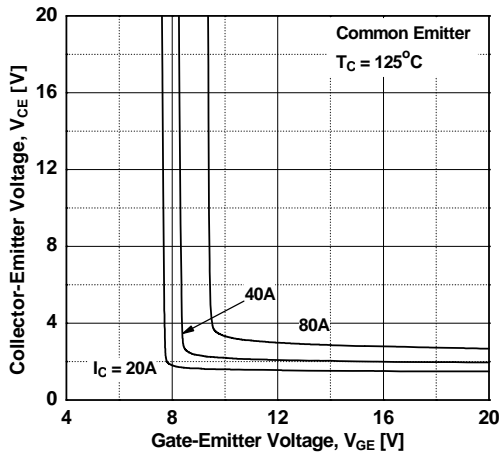


Figure 8. Capacitance Characteristics

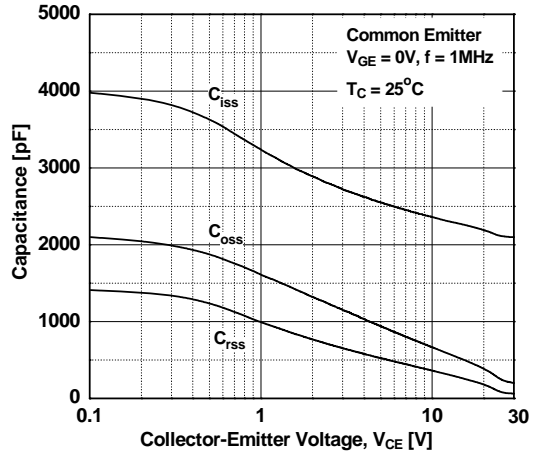


Figure 9. Gate Charge Characteristics

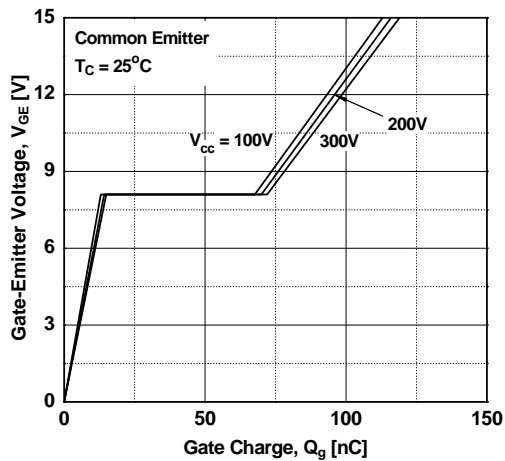


Figure 10. SOA Characteristics

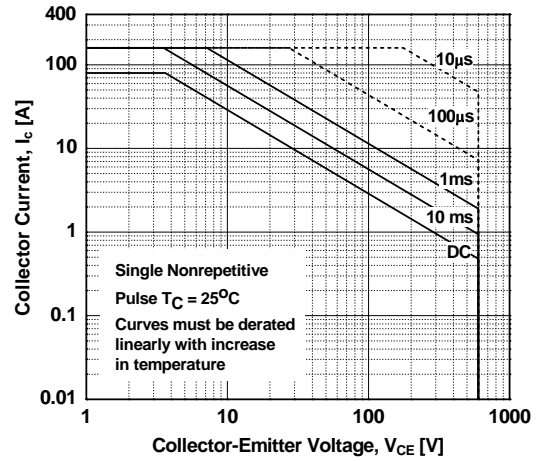


Figure 11. Turn-Off Switching SOA Characteristics

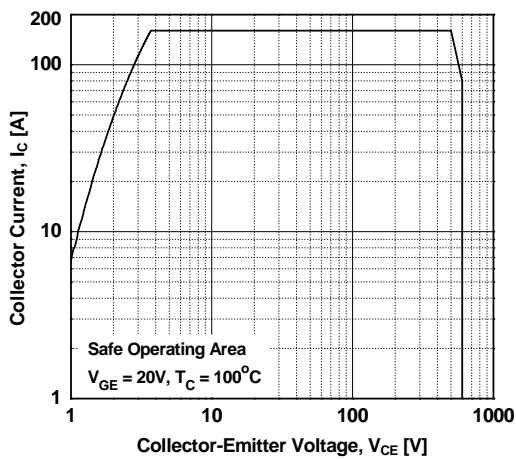
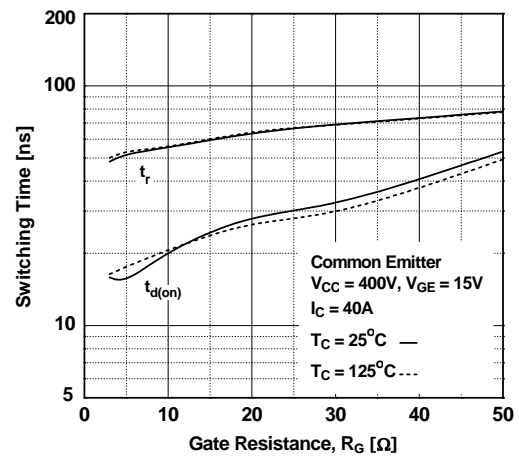


Figure 12. Turn-On Characteristics vs. Gate Resistance



Typical Performance Characteristics (Continued)

Figure 13. Turn-Off Characteristics vs. Gate Resistance

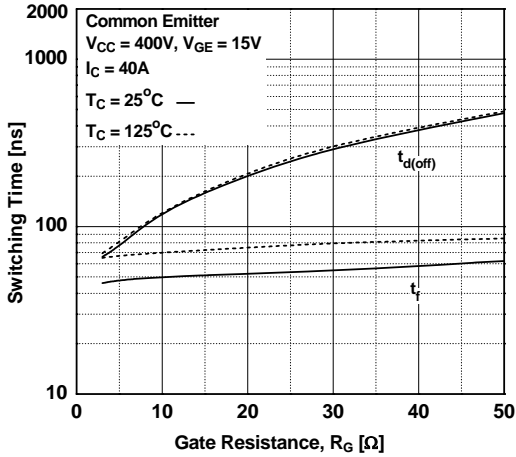


Figure 14. Turn-On Characteristics vs. Collector Current

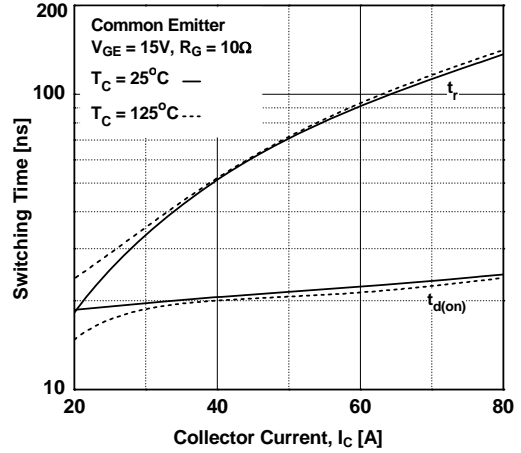


Figure 15. Turn-Off Characteristics vs. Collector Current

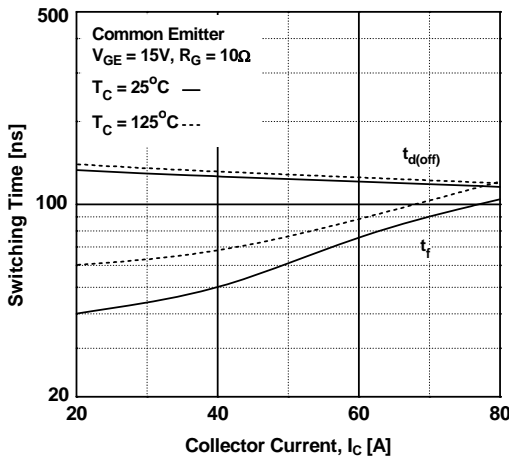


Figure 16. Switching Loss vs Gate Resistance

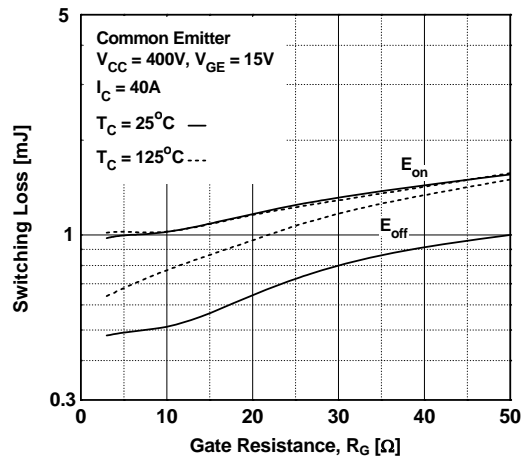
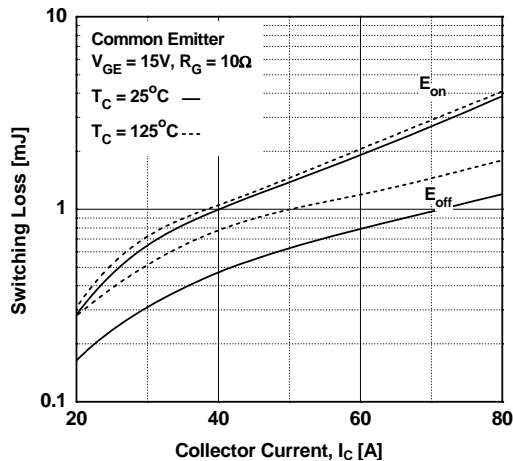


Figure 17. Switching Loss vs Collector Current



Typical Performance Characteristics (Continued)

Figure 18. Transient Thermal Impedance of IGBT

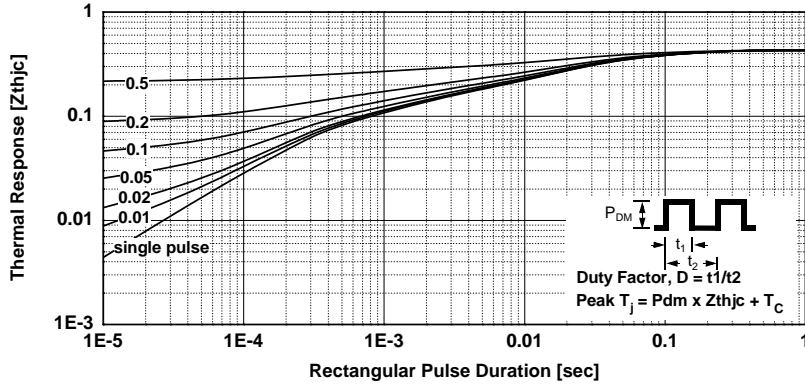


Figure 19. Typical Forward Voltage Drop

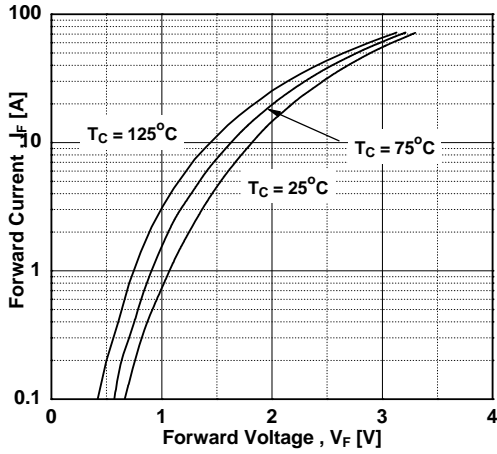


Figure 20. Stored Charge

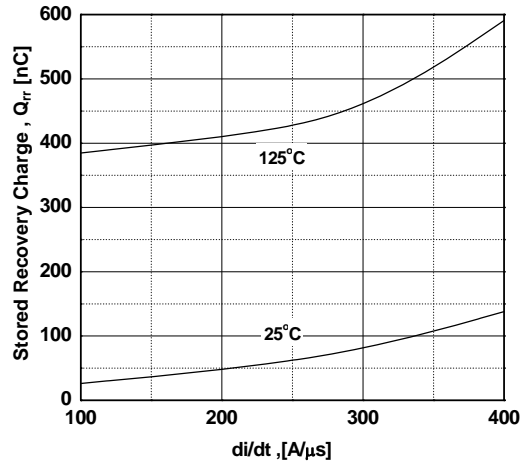


Figure 21. Reverse Recovery Time

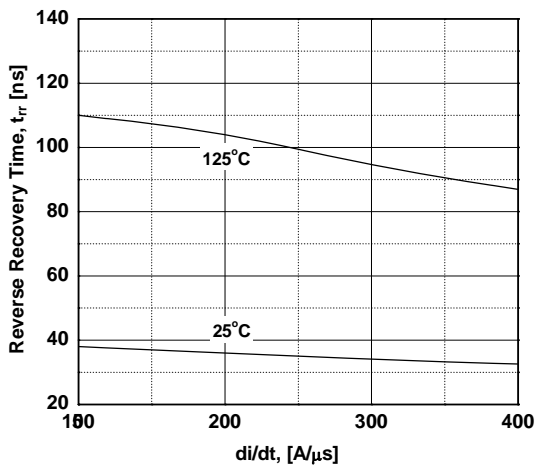
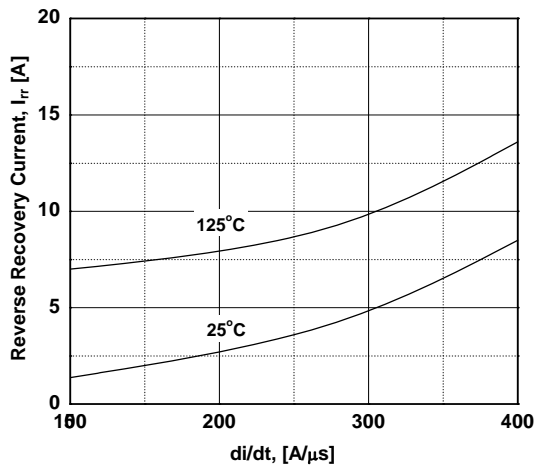


Figure 22. Reverse Recovery Current





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FRFET®	Power220®	SuperSOT™-3	UniFET™
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PRODUCT STATUS DEFINITIONS

Definition of Terms

Datasheet Identification	Product Status	Definition
Advance Information	Formative or In Design	This datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
Preliminary	First Production	This datasheet contains preliminary data; supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve design.
No Identification Needed	Full Production	This datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve design.
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